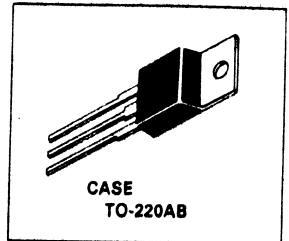


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**2N6394  
 thru  
 2N6399  
 MCR220-5  
 MCR220-7  
 MCR220-9**



**\*MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage ( $T_J = -40$ to $125^\circ\text{C}$ )	$V_{RRM}$ or $V_{DRM}$	50 100 200 300 400 500 600 700 800	Volts
RMS On-State Current (All Conduction Angles)	$I_{T(RMS)}$	12	Amps
Peak Non-Repetitive Surge Current (1/2 cycle, Sine Wave, 60 Hz, $T_J = 125^\circ\text{C}$ )	$I_{TSM}$	100	Amps
Circuit Fusing ( $T_J = -40$ to $+125^\circ\text{C}$ , $t = 1$ to $8.3$ ms)	$I^2t$	40	$\text{A}^2\text{s}$
Forward Peak Power	PGM	20	Watts
Forward Average Gate Power	PG(AV)	0.5	Watt

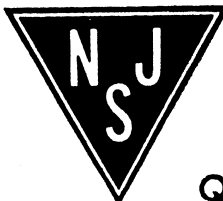
Rating	Symbol	Value	Unit
Forward Peak Gate Current	$I_{GM}$	2	Amps
Operating Junction Temperature Range	$T_J$	-40 to +125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-40 to +150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$  unless otherwise noted.)**

Characteristic	Symbol	Min	Typ	Max	Unit
*Peak Forward or Reverse Blocking Current (Rated $V_{DRM}$ or $V_{RRM}$ ) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	$I_{DRM}$ , $I_{RRM}$	—	—	10 2	$\mu\text{A}$ mA
*Forward "On" Voltage ( $I_{TM} = 24$ A Peak)	$V_{TM}$	—	1.7	2.2	Volts
*Gate Trigger Current (Continuous dc) ( $V_D = 12$ Vdc, $R_L = 100$ Ohms)	$I_{GT}$	—	5	30	mA
*Gate Trigger Voltage (Continuous dc) ( $V_D = 12$ Vdc, $R_L = 100$ Ohms) ( $V_D = \text{Rated } V_{DRM}$ , $R_L = 100$ Ohms, $T_J = 125^\circ\text{C}$ )	$V_{GT}$ $V_{GD}$	— 0.2	0.7 —	1.5 —	Volts
*Holding Current ( $V_D = 12$ Vdc)	$I_H$	—	6	40	mA
Turn-On Time ( $I_{TM} = 12$ A, $I_{GT} = 40$ mAdc, $V_D = \text{Rated } V_{DRM}$ )	$t_{gt}$	—	1	2	$\mu\text{s}$
Turn-Off Time ( $V_D = \text{Rated } V_{DRM}$ ) ( $I_{TM} = 12$ A, $I_R = 12$ A) ( $I_{TM} = 12$ A, $I_R = 12$ A, $T_J = 125^\circ\text{C}$ )	$t_q$	—	15 35	—	$\mu\text{s}$
Critical Rate-of-Rise of Off-State Voltage Exponential ( $V_D = \text{Rated } V_{DRM}$ , $T_J = 125^\circ\text{C}$ )	dv/dt	—	50	—	$\text{V}/\mu\text{s}$



**Quality Semi-Conductors**